

**Amendments to the Specification**

Please replace the paragraph beginning on page 22, line 22, with the following rewritten paragraph:

In Fig. 1, in addition to a first isolation region 300 for isolating each of the transistors, two second isolation regions 140 and 142 formed by a LOCOS process in the same manner as the first isolation region are formed. An  $N^+$  region 154 is formed between the second isolation regions 140 and 142. A  $P^+$  region 156 connected to the P-type well of the semiconductor substrate is formed in the region isolated from the  $N^+$  region 154 by the second isolation region 142. These regions are referred to as second diffusion regions.

Please replace the paragraph beginning on page 23, line 12, with the following rewritten paragraph:

An NPN lateral bipolar transistor 150 is formed by a collector 152 formed in the same  $N^+$  diffusion region as the drain 114, an emitter formed by the  $N^+$  region 154 (hereinafter may be called emitter 154), and a base region combining the  $B^{11+}$  doped region 150 in the P-type well and its surroundings in the P-type well. A base contact is formed by the  $P^+$  region 156 connected to the P-type well (hereinafter may be called base contact 156). Fig. 1 shows a contact 158 connected to the emitter 154 and a contact 159 connected to the base contact 156, both of which are grounded.